

Corrections to “A Novel Dual-Directional SCR Structure With High Holding Voltage for 12-V Applications in 0.13- μm BCD Process”

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In Section I of the above article [1], the sentence beginning in the 18th line of the second column contains typos that misrepresent the range of voltages. The correct sentence is the following: “However, the strong snapback characteristics of a traditional SCR structure that are caused by high avalanche breakdown between the well regions allow it to have a substantially high trigger voltage (approximately 17–22 V) and low holding voltage (approximately 2–4 V).”

REFERENCES

- [1] K.-I. Do, B.-B. Song, and Y.-S. Koo, “A novel dual-directional SCR structure with high holding voltage for 12-V applications in 0.13- μm BCD process,” *IEEE Trans. Electron Devices*, vol. 67, no. 11, pp. 5020–5027, Nov. 2020.

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